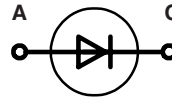
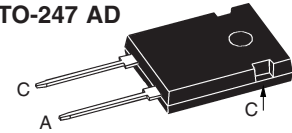
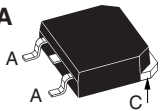


Fast Recovery Epitaxial Diode (FRED)

$V_{RRM} = 600\text{ V}$
 $I_{FAVM} = 60\text{ A}$
 $t_{rr} = 35\text{ ns}$

V_{RSM}	V_{RRM}	Type
V	V	
600	600	DSEI 60-06A
600	600	DSEI 60-06AT


TO-247 AD

TO-268 AA (AT Type)


A = Anode, C = Cathode

Symbol	Conditions	Maximum Ratings	
I_{FRMS}	$T_{VJ} = T_{VJM}$	100	A
I_{FAVM} ①	$T_C = 70^\circ\text{C}$; rectangular, $d = 0.5$	60	A
I_{FRM}	$t_p < 10\ \mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	800	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	550	A
	$t = 8.3\text{ ms}$ (60 Hz), sine	600	A
	$T_{VJ} = 150^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	480	A
	$t = 8.3\text{ ms}$ (60 Hz), sine	520	A
I^2t	$T_{VJ} = 45^\circ\text{C}$ $t = 10\text{ ms}$ (50 Hz), sine	1510	A^2s
	$t = 8.3\text{ ms}$ (60 Hz), sine	1490	A^2s
	$T_{VJ} = 150^\circ\text{C}$; $t = 10\text{ ms}$ (50 Hz), sine	1150	A^2s
	$t = 8.3\text{ ms}$ (60 Hz), sine	1120	A^2s
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-40...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	166	W
M_d	Mounting torque	0.8...1.2	Nm
Weight		6	g

Features

- International standard package JEDEC TO-247 AD
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low I_{RM} -values
- Soft recovery behaviour
- Epoxy meets UL 94V-0

Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses
- Operating at lower temperature or space saving by reduced cooling

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R	$T_{VJ} = 25^\circ\text{C}$; $V_R = V_{RRM}$		200 μA
	$T_{VJ} = 25^\circ\text{C}$; $V_R = 0.8 \cdot V_{RRM}$		100 μA
	$T_{VJ} = 125^\circ\text{C}$; $V_R = 0.8 \cdot V_{RRM}$		14 mA
V_F	$I_F = 16\text{ A}$; $T_{VJ} = 150^\circ\text{C}$		1.5 V
	$T_{VJ} = 25^\circ\text{C}$		1.8 V
V_{T0}	For power-loss calculations only		1.13 V
r_T	$T_{VJ} = T_{VJM}$		4.7 m Ω
R_{thJC}			0.75 K/W
R_{thCH}	(version A)	0.25	K/W
t_{rr}	$I_F = 1\text{ A}$; $-di/dt = 200\text{ A}/\mu\text{s}$; $V_R = 30\text{ V}$; $T_{VJ} = 25^\circ\text{C}$	35	50 ns
I_{RM}	$V_R = 350\text{ V}$; $I_F = 60\text{ A}$; $-di_p/dt = 480\text{ A}/\mu\text{s}$ $L \leq 0.05\ \mu\text{H}$; $T_{VJ} = 100^\circ\text{C}$	4	4.4 A

① I_{FAVM} rating includes reverse blocking losses at T_{VJM} , $V_R = 0.8 V_{RRM}$, duty cycle $d = 0.5$
 Data according to IEC 60747

IXYS reserves the right to change limits, test conditions and dimensions

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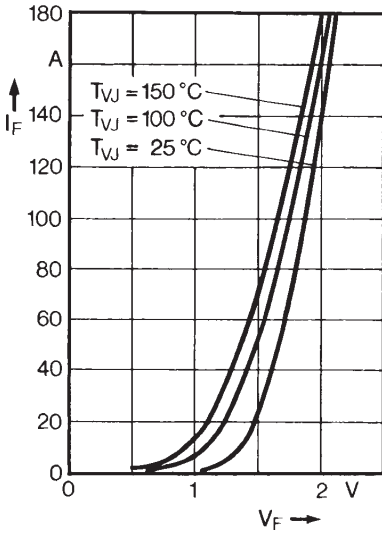


Fig. 1 Forward current versus voltage drop.

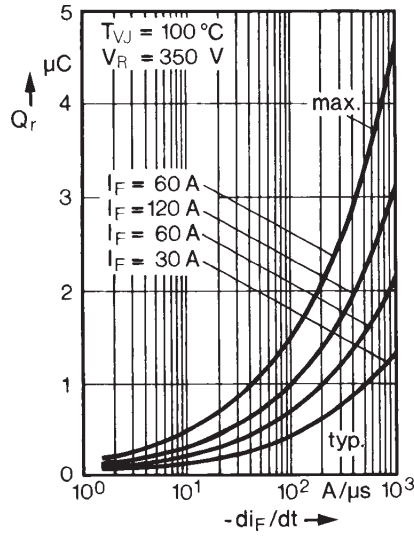


Fig. 2 Recovery charge versus $-di_F/dt$.

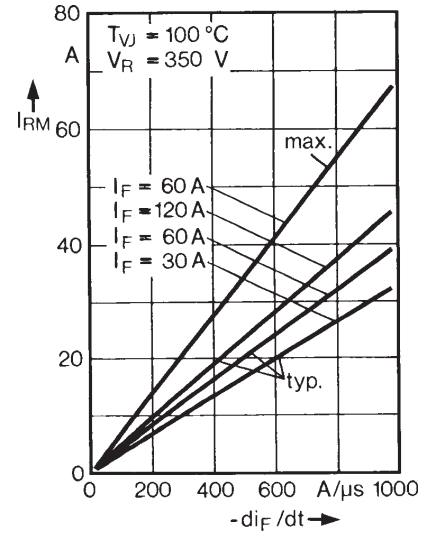


Fig. 3 Peak reverse current versus $-di_F/dt$.

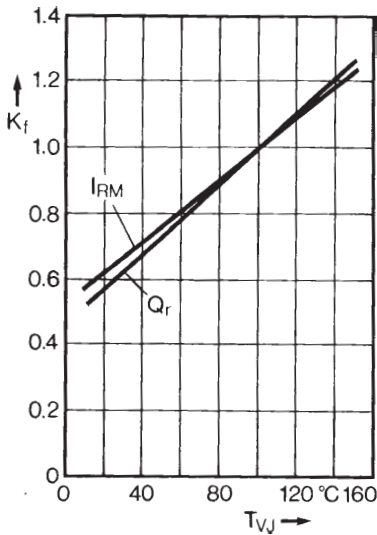


Fig. 4 Dynamic parameters versus junction temperature.

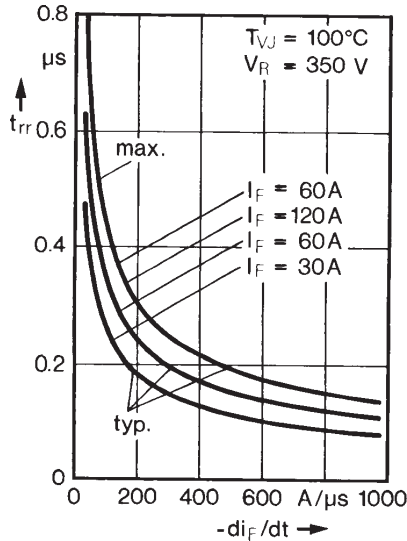


Fig. 5 Recovery time versus $-di_F/dt$.

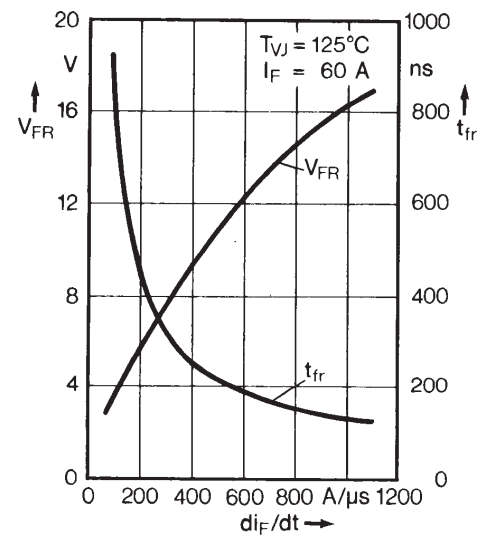


Fig. 6 Peak forward voltage versus di_F/dt .

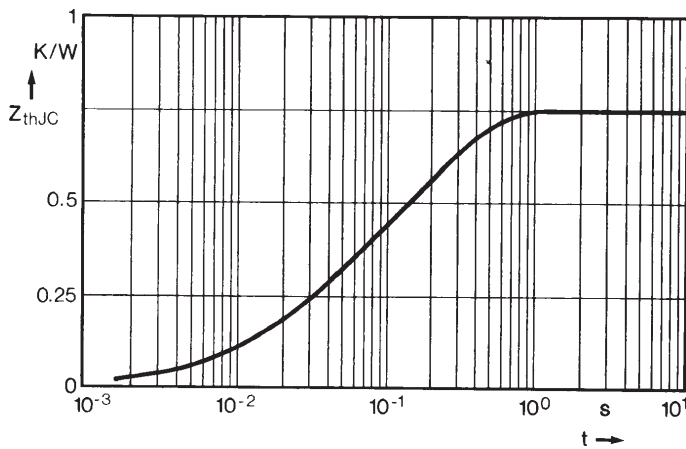
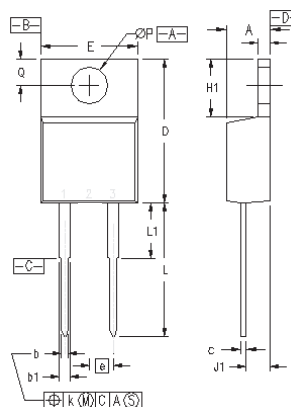


Fig. 7 Transient thermal impedance junction to case.

Dimensions



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.83	0.170	0.190
b	0.64	1.02	0.025	0.040
b1	1.15	1.65	0.045	0.065
c	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	2.54 BSC		0.100 BSC	
F	1.14	1.40	0.045	0.055
H1	5.85	6.85	0.230	0.270
J1	2.29	2.79	0.090	0.110
k	0	0.38	0	0.015
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.53	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125